

AMENDMENTS TO THE SPECIFICATION

Please replace the section headings beginning at page 6, line 1 with the following rewritten section heading:

~~-- DISCLOSURE OF THE INVENTION~~

~~PROBLEMS TO BE SOLVED BY THE INVENTION~~SUMMARY OF THE INVENTION --

Please DELETE the section heading at page 6, line 15.

Please DELETE the section heading at page 7, line 20.

Please replace the paragraphs beginning at page 8, line 12 to page 9, line 12 with the following rewritten paragraphs:

-- ~~Fig. 1 is a~~Figs. 1(a) – (d) are cross-sectional ~~view~~views for illustrating the manufacturing process of a Schottky diode related to an embodiment of the present invention.;

~~Fig.2 is a~~ graph showing the relationship among a heat treatment temperature, the Schottky barrier height, and an n-factor.; and

~~Fig.3 is a~~ graphFigs. 3(a) – (b) are graphs showing the results of the measurement, respectively, of forward and reverse current/ voltage for the Schottky diode that has been obtained by the manufacturing process related to the present invention. ~~Fig.3(a)~~ shows the forward characteristics, and ~~Fig. 3(b)~~ shows the reverse characteristics.

EXPLANATIONS OF LETTERS OR NUMERALS

1: ~~SiC monocrystal substrate~~

2: ~~SiC epitaxial layer~~

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- ~~3: Ion implanted injection layer~~
- ~~4: SiO₂ oxide film~~
- ~~5: SiO₂ oxide film~~
- ~~6: Nickel film~~
- ~~7: Ohmic electrode~~
- ~~8: Molybdenum film --~~

-- ~~BEST MODE OF CARRYING OUT~~DETAILED DESCRIPTION OF THE
INVENTION --